Diode
Fast

RoHS Compliant

Features:

- Glass passivated chip junction
- High efficiency, low V_F
- High current capability
- High reliability
- High surge current capability
- For use in low voltage, high frequency inventor, free wheeling, and polarity protection application

Specifications:

Mechanical Data:

Cases	: Moulded plastic DO-41
Lead	: Pure tin plated, lead free, solderable per MIL-STD-202, Method 208 guaranteed
Polarity	: Colour band denotes cathode end
High temperature soldering guaranteed	: 260°C/10 seconds/0.375", (9.5mm) lead lengths at 5lbs., (2.3kg) tension
Weight	: 0.34g

Maximum Ratings and Electrical Characteristics:

Rating at 25°C ambient temperature unless otherwise specified.
Single phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

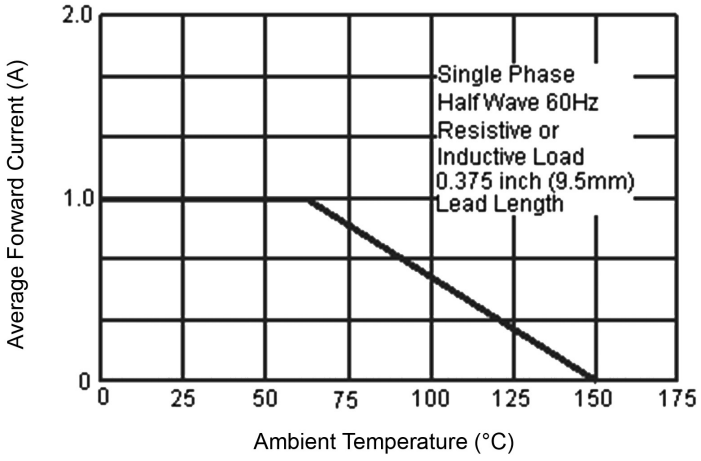
Type Number	Symbol	HER102G	HER104G	HER106G	HER108G	Units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	100	300	600	1,000	V
Maximum RMS Voltage	V_{RMS}	70	210	420	700	
Maximum DC Blocking Voltage	V_{DC}	100	300	600	1,000	
Maximum Average Forward Rectified Current 0.375" (9.5mm) Lead Length at T_A = 55°C	$I_{(AV)}$	1				A
Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	30				
Maximum Instantaneous Forward Voltage at 1A	V_F	1		1.7		V

Type Number	Symbol	HER102G	HER104G	HER106G	HER108G	Units
Maximum DC Reverse Current at T_A = 25°C at Rated DC Blocking Voltage at T_A = 125°C	I_R	5 150				µA µA
Maximum Reverse Recovery Time (Note 1)	T_{rr}	50		75		nS
Typical Junction Capacitance (Note 2)	C_j	15		10		pF
Typical Thermal Resistance	$R_{\theta JA}$ $R_{\theta JC}$	70 15				°C/W
Operating Temperature Range	T_J	-65 to +150				°C
Storage Temperature Range	T_{STG}					

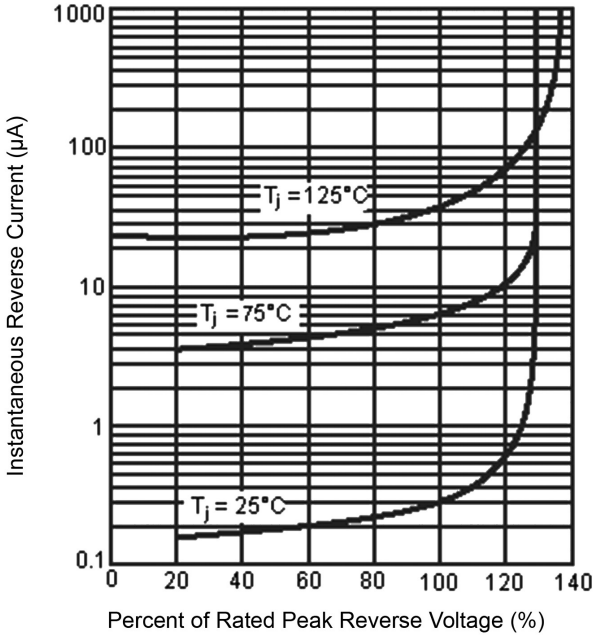
Note: 1. Reverse Recovery Test Conditions: I_F = 0.5A, I_R = 1A, I_{RR} = 0.25A.
Note: 2. Measured at 1MHz and Applied Reverse Voltage of 4V DC.
Note: 3. Mount on Cu-Pad Size 5mm × 5mm on PCB.

Ratings and Characteristic Curves (HER102G, HER104G, HER106G, HER108G)

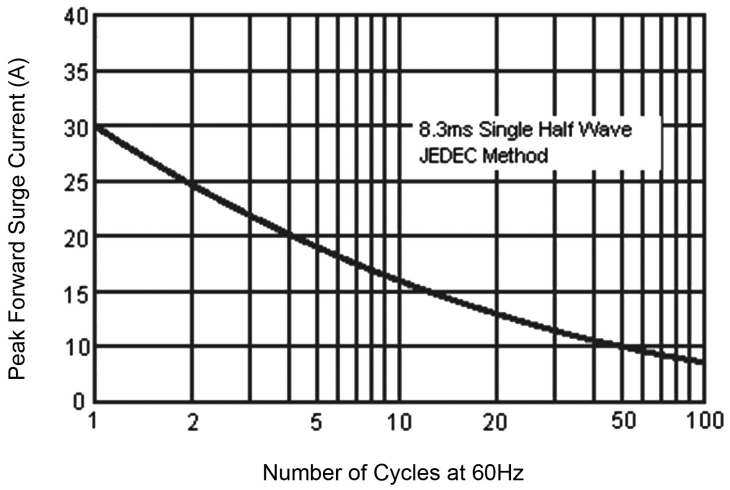
Maximum Forward Current Derating Curve



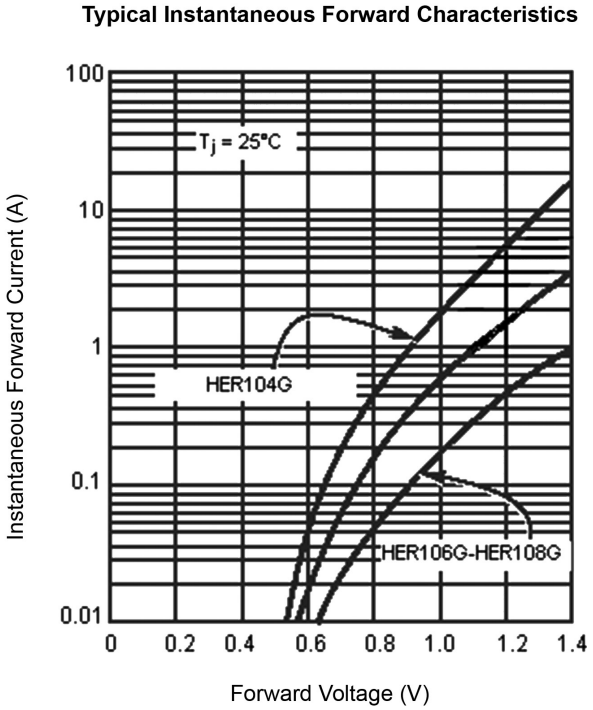
Typical Reverse Characteristics



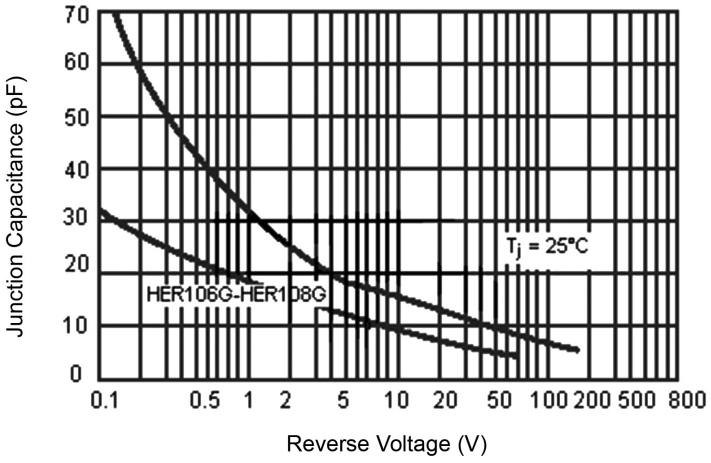
Maximum Non-Repetitive Forward Surge Current



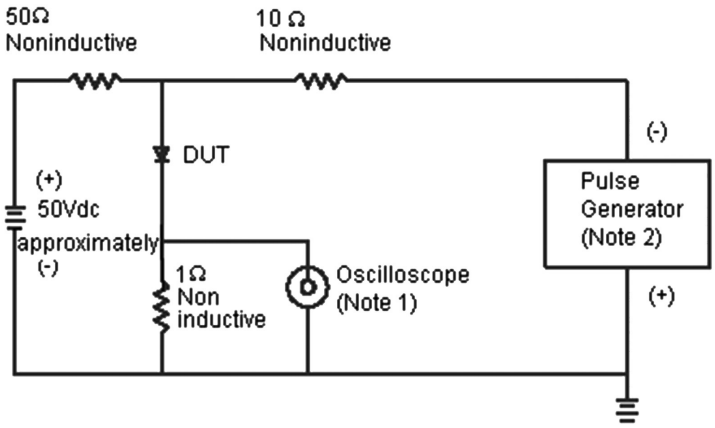
Typical Instantaneous Forward Characteristics

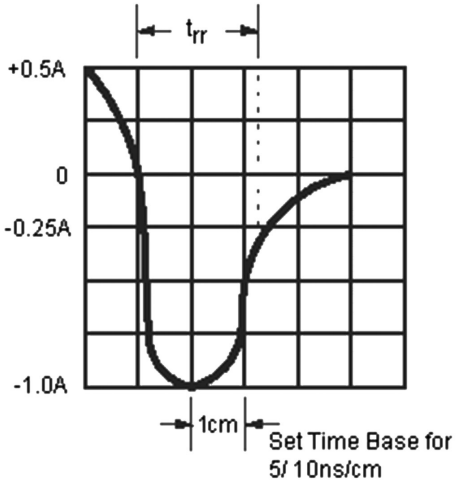


Typical Junction Capacitance



Reverse Recovery Time Characteristic and Test Circuit Diagram





Note: 1. Rise Time = 7ns Maximum Input Impedance = 1MΩ 22pf
Note: 2. Rise Time = 10ns Maximum Source Impedance = 50Ω

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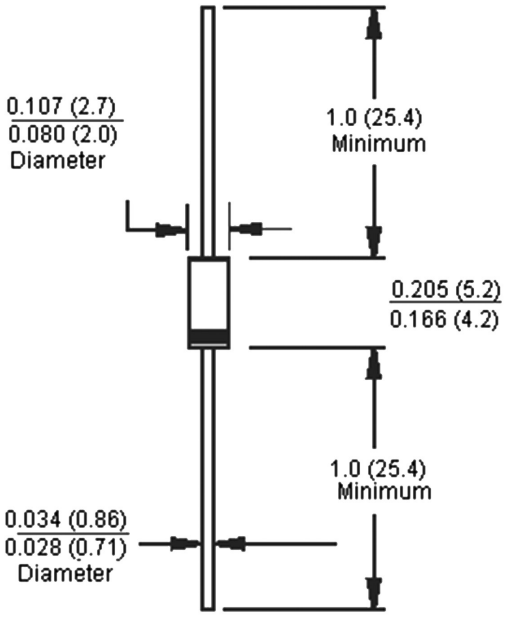

Dimensions : Inches (Millimetres)

Part Number Table

Description	Part Number
Diode, Fast, 1A, 100V	HER102G
Diode, Fast, 1A, 300V	HER104G
Diode, Fast, 1A, 600V	HER106G
Diode, Fast, 1A, 1,000V	HER108G

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